



DMP2100UQ

Product Summary

BV _{DSS}	Rds(on) max	Package	I _D T _A = +25°C
	38mΩ @ Vgs = -10V		-4.3A
-20V	43mΩ @ V _{GS} = -4.5V SOT23	SOT23	-4.0A
	75mΩ @ V _{GS} = -2.5V		-2.8A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Load Switch
- **Power Management Functions**
- Motor Control

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD** Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2100UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

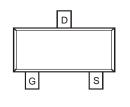
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (93)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

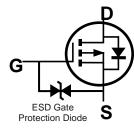






Top View





Top View Pin Configuration

Equivalent Circuit (Note 4)

Ordering Information (Note 5)

	Part Number	Compliance	Case	Packaging
	DMP2100UQ-7 Automotive		SOT23	3,000/Tape & Reel
Notes:	1. No purposely added lead.	Fully EU Directive 2002/95/EC (RoHS), 20	11/65/EU (RoHS 2) & 2015/863/EU (RoHS	3) compliant.

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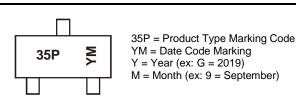
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum VGSS rating (given on page 2) can be applied.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Date Code Key												
Year	2008	~	2017	2018	3 201	9 20	020 2	2021	2022	2023	2024	2025
Code	V	~	E	F	G		H	Ι	J	К	L	М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

SOT23



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage		Vdss	-20	V	
Gate-Source Voltage (Note 6)			Vgss	±10	V
	Steady State	T _A = +25°C T _A = +70°C	ID	-4.3 -3.4	A
Continuous Drain Current (Note 8) V _{GS} = -10V	t<5s	T _A = +25°C T _A = +70°C	ID	-5.5 -4.3	A
Maximum Continuous Body Diodes Forward Curr	3)	ls	-2	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 7		I _{DM}	-30	A	
Pulsed Body Diodes Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	-30	А

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Tetal Dower Dissinction (Nate 7)	T _A = +25°C	P	0.8	W	
otal Power Dissipation (Note 7)	T _A = +70°C	PD	0.5		
Thermal Decistors a Junction to Ambient (Note 7)	Steady State	P	161	°C/W	
Thermal Resistance, Junction to Ambient (Note 7)	t<5s	Reja	96	0/00	
Total Dower Dissinction (Note 9)	T _A = +25°C	P	1.3	W	
Total Power Dissipation (Note 8)	T _A = +70°C	PD	0.8		
Thermal Desistance, Junction to Ambient (Note 9)	Steady State	Devi	99	°C/W	
Thermal Resistance, Junction to Ambient (Note 8)	t<5s	Reja	60		
Thermal Resistance, Junction to Case (Note 8)		R _{ejc}	15		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)	Symbol	IVIIII	тур	IVIAX	Unit	Test condition
Drain-Source Breakdown Voltage	BV _{DSS}	-20		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current			_	-1	μÂ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	_		±10	μΑ	$V_{\rm DS} = \pm 20^{\circ}, \ V_{\rm GS} = 0^{\circ}$ $V_{\rm GS} = \pm 8^{\circ}, \ V_{\rm DS} = 0^{\circ}$
ON CHARACTERISTICS (Note 9)	1635			10	μπ	VGS = ±0V, VDS = 0V
Gate Threshold Voltage	VGS(TH)	-0.3	_	-1.4	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
		_	25	38		$V_{GS} = -10V, I_D = -3.5A$
		_	29	43		$V_{GS} = -4.5V, I_{D} = -3A$
Static Drain-Source On-Resistance	RDS(ON)	_	37	75	mΩ	Vgs = -2.5V, ID = -1A
		_	47			$V_{GS} = -1.8V, I_{D} = -0.5A$
Forward Transfer Admittance	Y _{fs}	_	3	—	S	$V_{DS} = -5V, I_{D} = -4A$
DYNAMIC CHARACTERISTICS (Note 10)			1	1		
Input Capacitance	Ciss	_	216		pF	
Output Capacitance	Coss	_	90		pF	Vps = -15V, Vgs = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	—	24	—	pF	
Gate Resistance	Rg	_	250		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 10)						•
Total Gate Charge	Qg	—	9.1	_	nC	
Gate-Source Charge	Qgs	_	1.6		nC	$V_{GS} = -4.5V, V_{DS} = -10V$
Gate-Drain Charge	Qgd	—	2.0	—	nC	$-I_D = -4A$
Turn-On Delay Time	t _{D(ON)}	_	80		ns	
Turn-On Rise Time	t _R	—	155		ns	V _{DS} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	tD(OFF)		688		ns	R _D = 2.5Ω, R _G = 3.0Ω
Turn-Off Fall Time	t _F		423		ns	

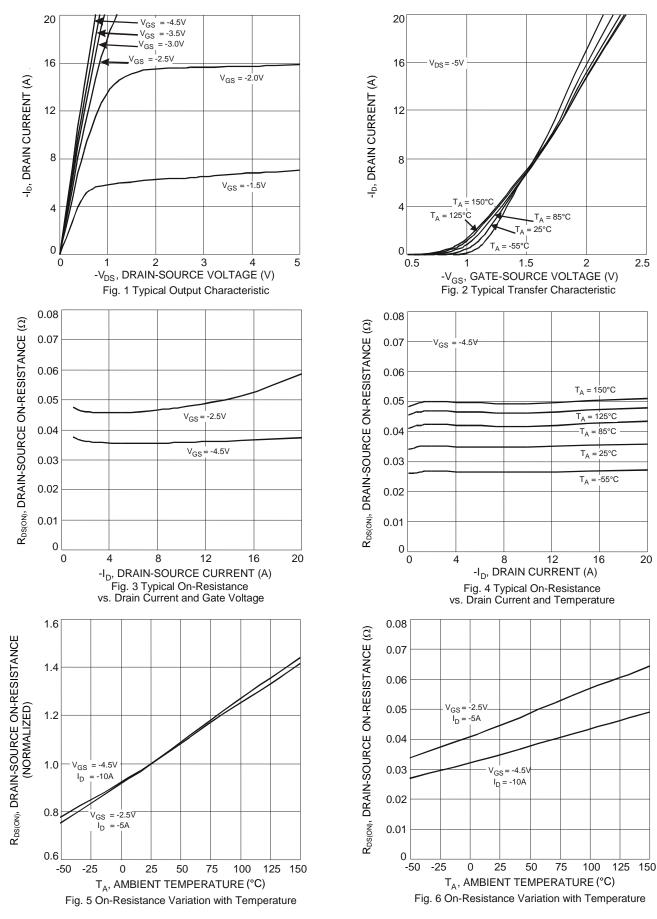
6. AEC-Q101 V_{GS} maximum is $\pm 9.6V.$ Notes:

7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
8. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

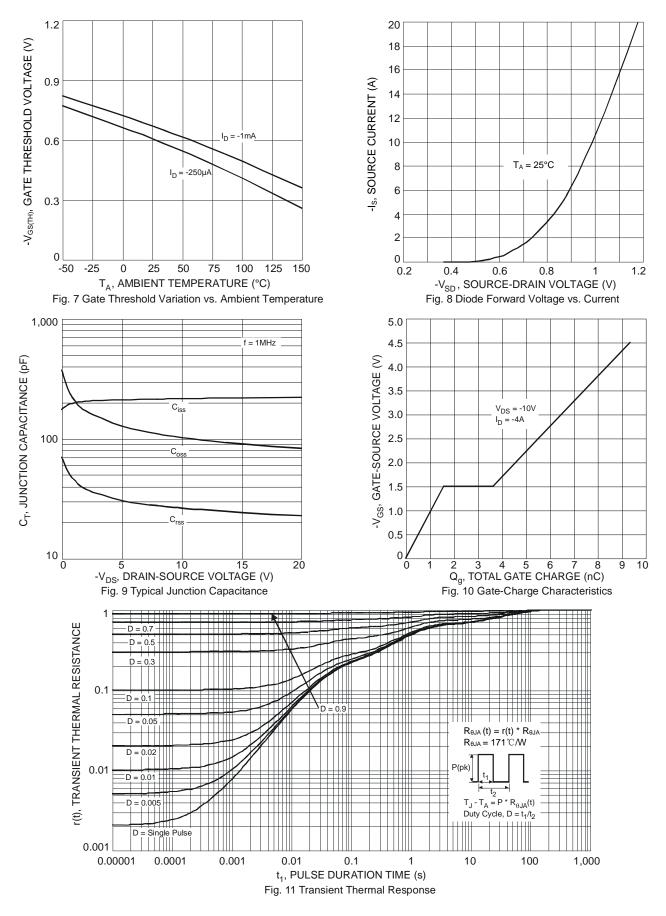
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



DMP2100UQ





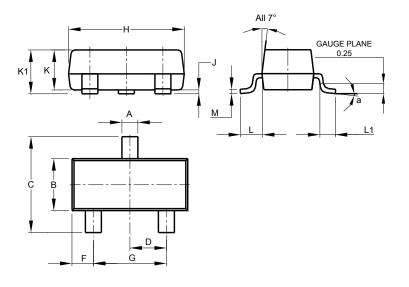




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

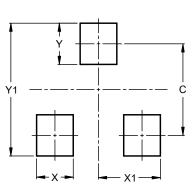
SOT23



	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
Н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
М	0.085	0.150	0.110						
а	0°	8°							
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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